FAIRCHILD SEMICONDUCTOR®

IGBT

SGP23N60UFD

Ultra-Fast IGBT

General Description

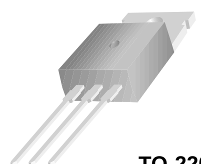
Fairchild's UFD series of Insulated Gate Bipolar Transistors (IGBTs) provides low conduction and switching losses. The UFD series is designed for applications such as motor control and general inverters where high speed switching is a required feature.

Features

- High speed switching
- Low saturation voltage : $V_{CE(sat)}$ = 2.1 V @ I_C = 12A
- High input impedance
- CO-PAK, IGBT with FRD : t_{rr} = 42ns (typ.)

Applications

AC & DC motor controls, general purpose inverters, robotics, and servo controls.



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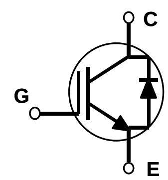

Absolute Maximum Ratings

T_C = 25°C unless otherwise noted

Symbol	Description		SGP23N60UFD	Units
V_{CES}	Collector-Emitter Voltage		600	V
V_{GES}	Gate-Emitter Voltage		± 20	V
I_C	Collector Current	@ T_C = 25°C	23	A
	Collector Current	@ T_C = 100°C	12	A
$I_{CM\ (1)}$	Pulsed Collector Current		92	A
I_F	Diode Continuous Forward Current	@ T_C = 100°C	12	A
I_{FM}	Diode Maximum Forward Current		92	A
P_D	Maximum Power Dissipation	@ T_C = 25°C	100	W
	Maximum Power Dissipation	@ T_C = 100°C	40	W
T_J	Operating Junction Temperature		-55 to +150	°C
T_{stg}	Storage Temperature Range		-55 to +150	°C
T_L	Maximum Lead Temp. for Soldering Purposes, 1/8" from Case for 5 Seconds		300	°C

Notes :
(1) Repetitive rating : Pulse width limited by max. junction temperature

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$(IGBT)	Thermal Resistance, Junction-to-Case	--	1.2	°C/W
$R_{\theta JC}$(DIODE)	Thermal Resistance, Junction-to-Case	--	2.5	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	62.5	°C/W

Electrical Characteristics of the IGBT T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
Off Characteristics						
BV_{CES}	Collector-Emitter Breakdown Voltage	V_{GE} = 0V, I_C = 250uA	600	--	--	V
$\Delta B_{VCES}/\Delta T_J$	Temperature Coefficient of Breakdown Voltage	V_{GE} = 0V, I_C = 1mA	--	0.6	--	V/°C
I_{CES}	Collector Cut-Off Current	$V_{CE} = V_{CES}$, V_{GE} = 0V	--	--	250	uA
I_{GES}	G-E Leakage Current	$V_{GE} = V_{GES}$, V_{CE} = 0V	--	--	± 100	nA
On Characteristics						
$V_{GE(th)}$	G-E Threshold Voltage	I_C = 12mA, $V_{CE} = V_{GE}$	3.5	4.5	6.5	V
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	I_C = 12A, V_{GE} = 15V	--	2.1	2.6	V
		I_C = 23A, V_{GE} = 15V	--	2.6	--	V
Dynamic Characteristics						
C_{ies}	Input Capacitance	V_{CE} = 30V, V_{GE} = 0V, f = 1MHz	--	720	--	pF
C_{oes}	Output Capacitance		--	100	--	pF
C_{res}	Reverse Transfer Capacitance		--	25	--	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{CC} = 300 V, I_C = 12A, R_G = 23Ω, V_{GE} = 15V, Inductive Load, T_C = 25°C	--	17	--	ns
t_r	Rise Time		--	27	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	60	130	ns
t_f	Fall Time		--	70	150	ns
E_{on}	Turn-On Switching Loss		--	115	--	uJ
E_{off}	Turn-Off Switching Loss		--	135	--	uJ
E_{ts}	Total Switching Loss		--	250	400	uJ
$t_{d(on)}$	Turn-On Delay Time	V_{CC} = 300 V, I_C = 12A, R_G = 23Ω, V_{GE} = 15V, Inductive Load, T_C = 125°C	--	23	--	ns
t_r	Rise Time		--	32	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	100	200	ns
t_f	Fall Time		--	220	250	ns
E_{on}	Turn-On Switching Loss		--	205	--	uJ
E_{off}	Turn-Off Switching Loss		--	320	--	uJ
E_{ts}	Total Switching Loss		--	525	800	uJ
Q_g	Total Gate Charge	V_{CE} = 300 V, I_C = 12A, V_{GE} = 15V	--	49	80	nC
Q_{ge}	Gate-Emitter Charge		--	11	17	nC
Q_{gc}	Gate-Collector Charge		--	14	22	nC
L_e	Internal Emitter Inductance	Measured 5mm from PKG	--	7.5	--	nH

Electrical Characteristics of DIODE T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions		Min.	Typ.	Max.	Units
V_{FM}	Diode Forward Voltage	I_F = 12A	T_C = 25°C	--	1.4	1.7	V
			T_C = 100°C	--	1.3	--	
t_{rr}	Diode Reverse Recovery Time	I_F = 12A, di/dt = 200A/us	T_C = 25°C	--	42	60	ns
			T_C = 100°C	--	80	--	
I_{rr}	Diode Peak Reverse Recovery Current		T_C = 25°C	--	3.5	6.0	A
			T_C = 100°C	--	5.6	--	
Q_{rr}	Diode Reverse Recovery Charge		T_C = 25°C	--	80	180	nC
			T_C = 100°C	--	220	--	

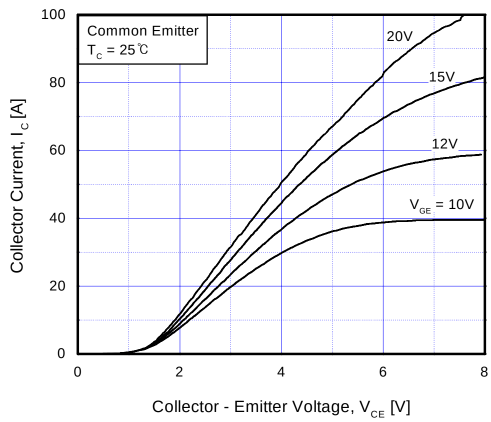

Fig 1. Typical Output Characteristics

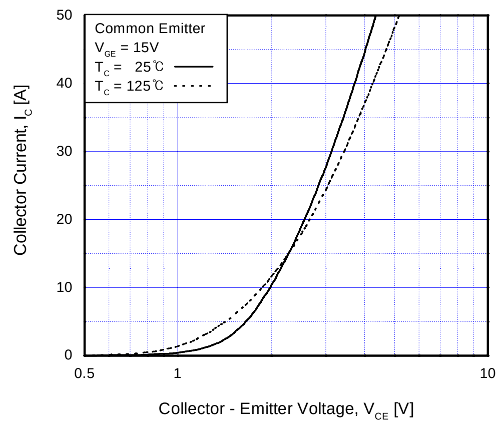

Fig 2. Typical Saturation Voltage Characteristics

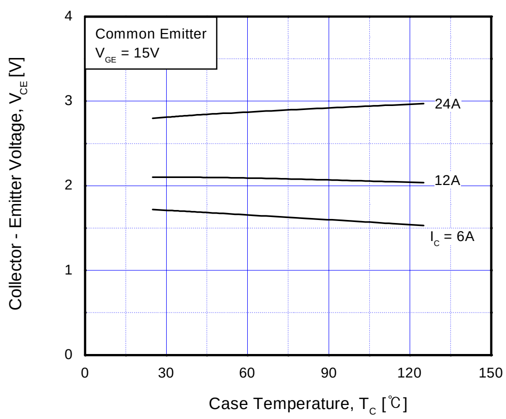

Fig 3. Saturation Voltage vs. Case Temperature at Variant Current Level

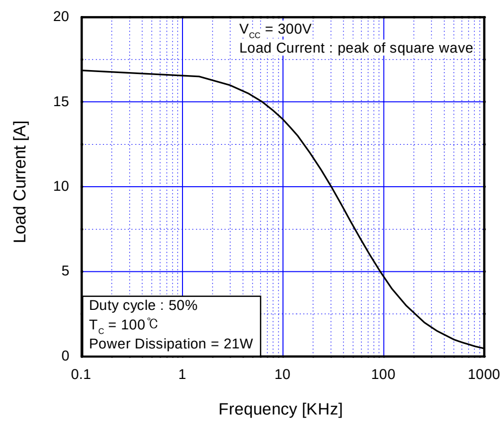

Fig 4. Load Current vs. Frequency

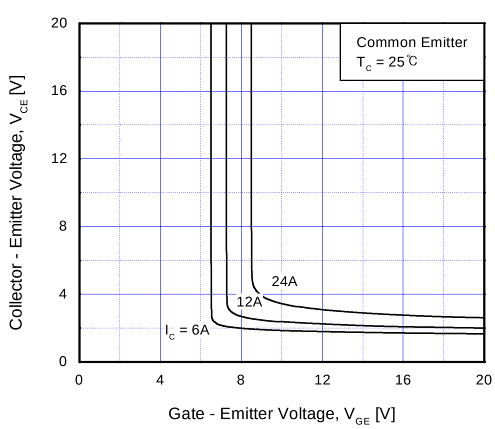

Fig 5. Saturation Voltage vs. V_{GE}

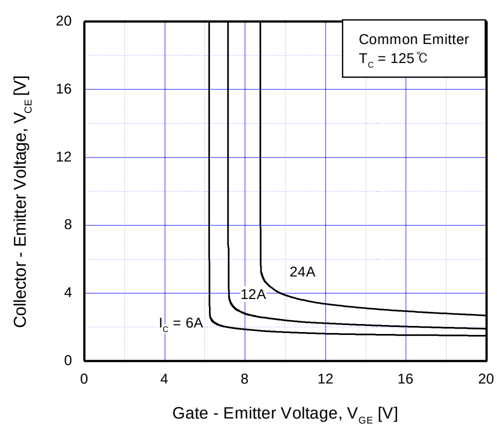

Fig 6. Saturation Voltage vs. V_{GE}

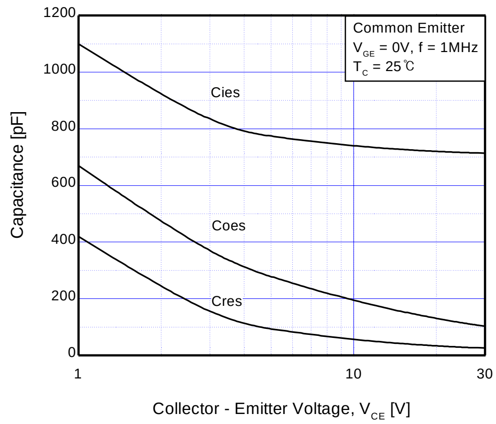

Fig 7. Capacitance Characteristics

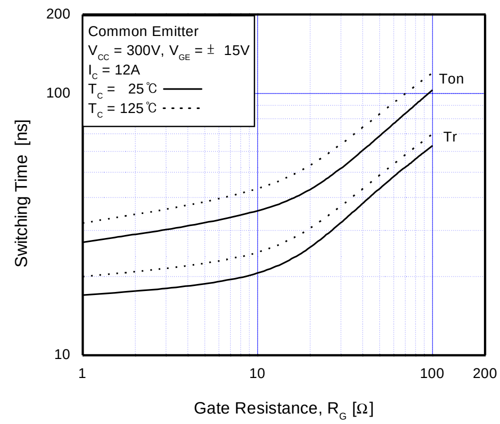

Fig 8. Turn-On Characteristics vs. Gate Resistance

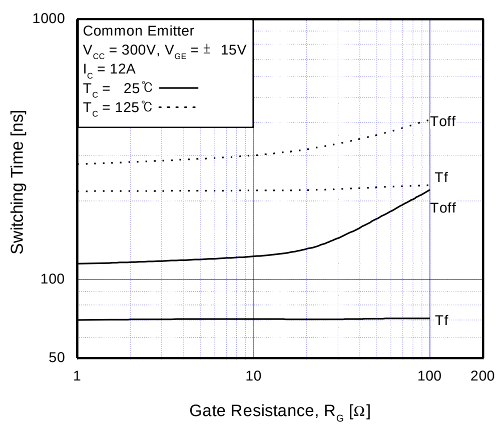

Fig 9. Turn-Off Characteristics vs. Gate Resistance

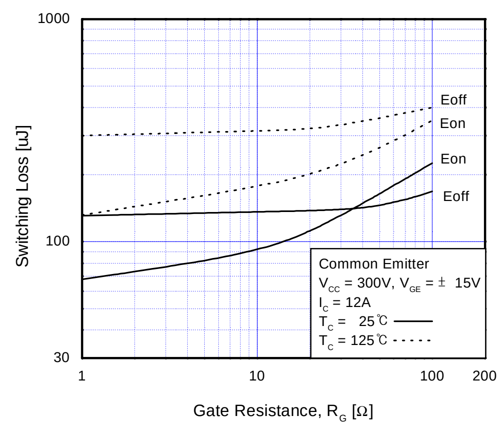

Fig 10. Switching Loss vs. Gate Resistance

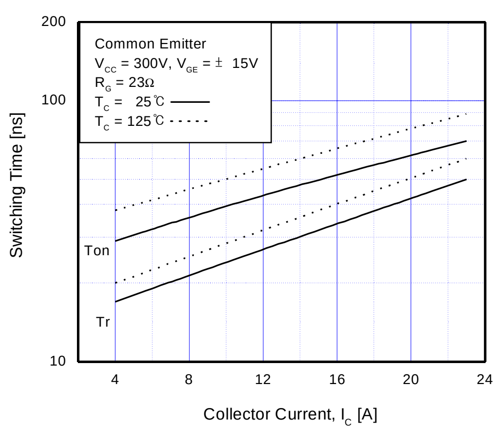

Fig 11. Turn-On Characteristics vs. Collector Current

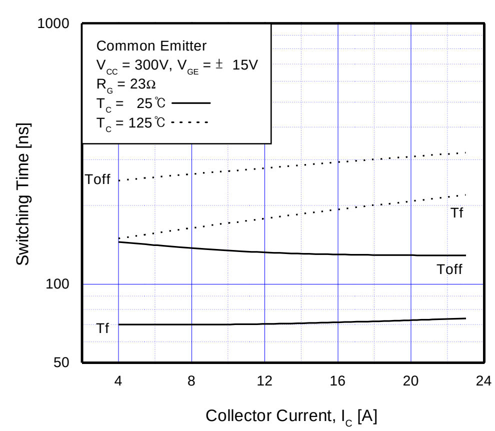

Fig 12. Turn-Off Characteristics vs. Collector Current

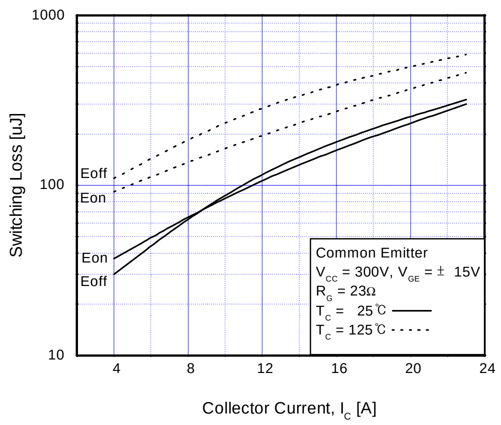

Fig 13. Switching Loss vs. Collector Current

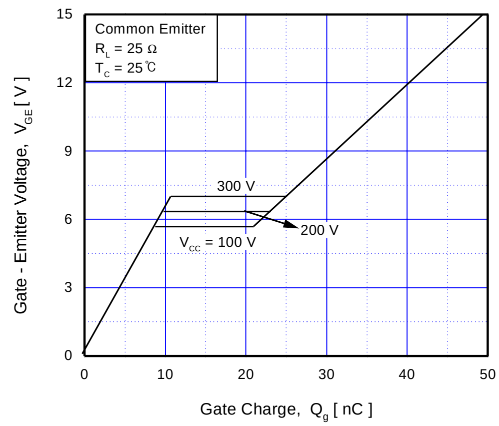

Fig 14. Gate Charge Characteristics

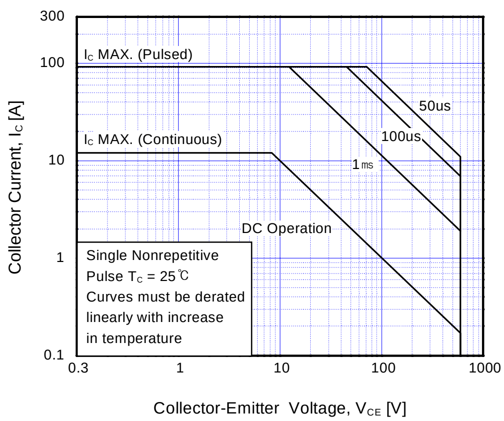

Fig 15. SOA Characteristics

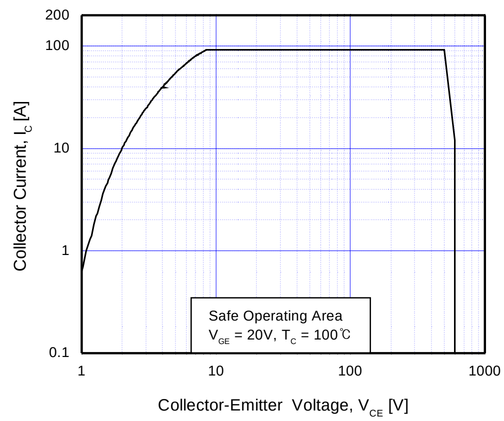

Fig 16. Turn-Off SOA Characteristics

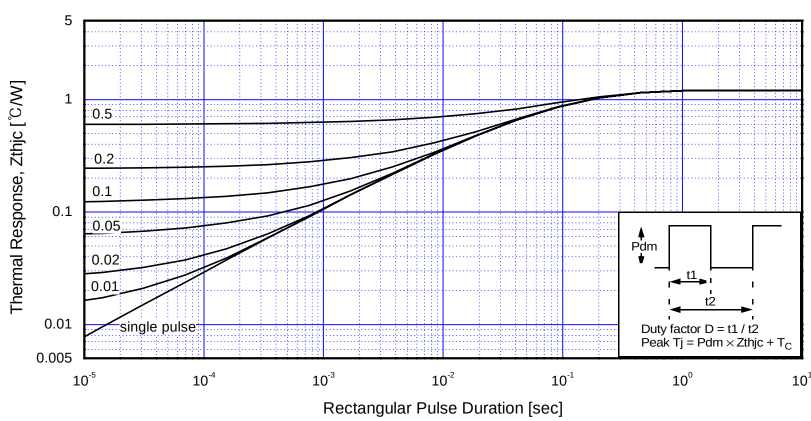

Fig 17. Transient Thermal Impedance of IGBT

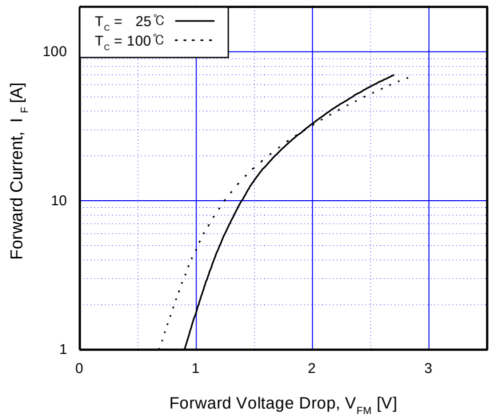

Fig 18. Forward Characteristics

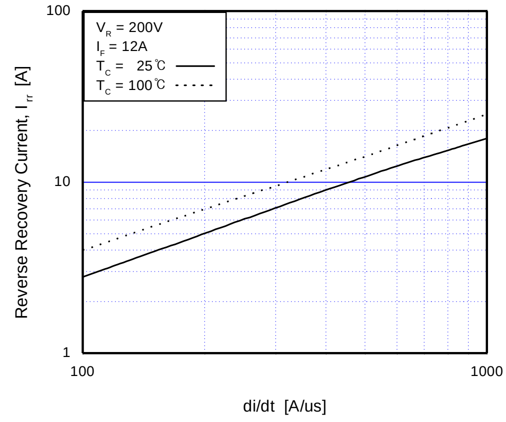

Fig 19. Reverse Recovery Current

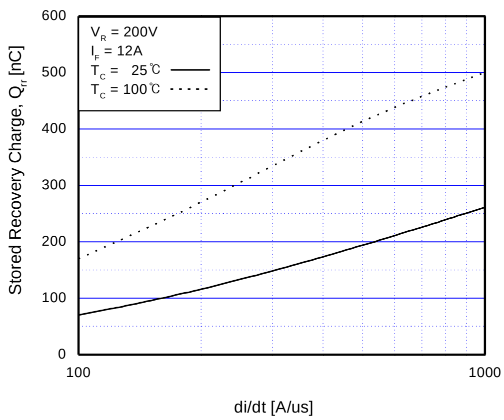

Fig 20. Stored Charge

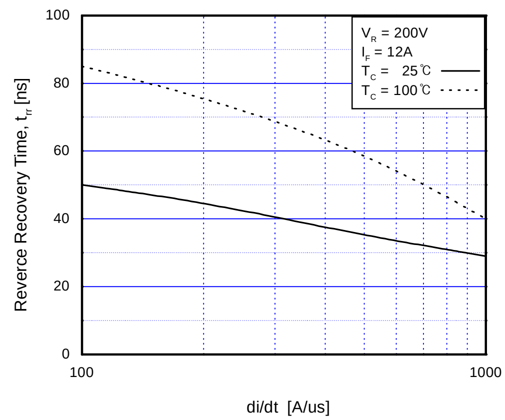

Fig 21. Reverse Recovery Time

Package Dimension

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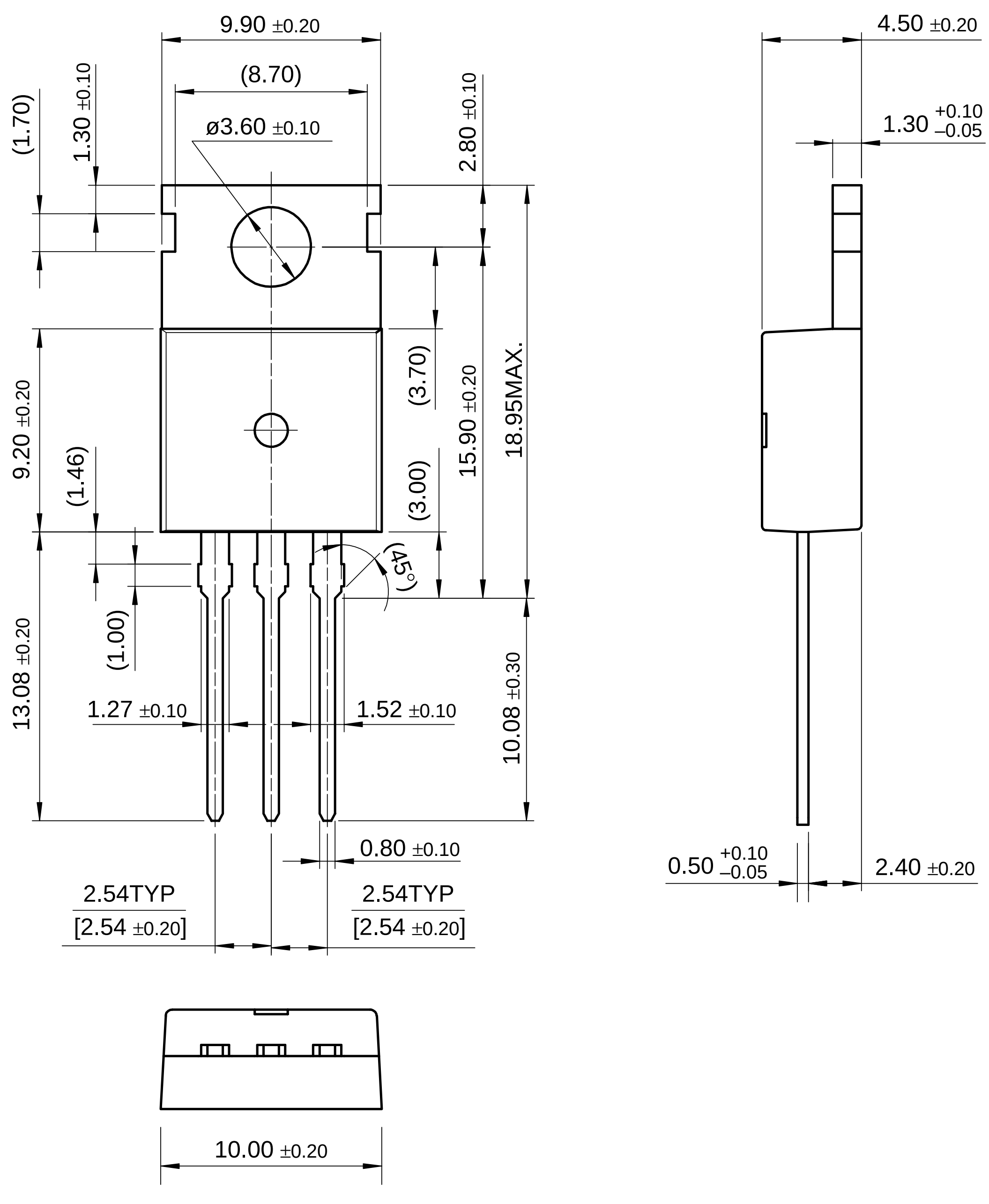

Dimensions in Millimeters

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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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